



STPS1545CT/CF/CG/CFP/CR

POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 x 7.5 A
V_{RRM}	45 V
$T_j(\text{max})$	175 °C
$V_F(\text{max})$	0.57 V

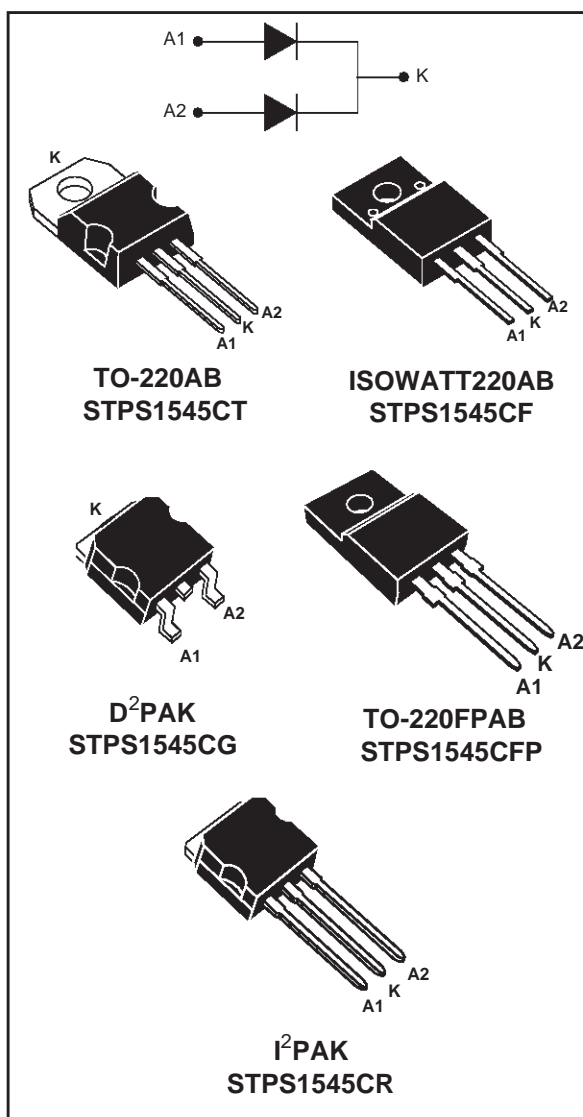
FEATURES AND BENEFITS

- Very small conduction losses
- Negligible switching losses
- Extremely fast switching
- Insulated package: ISOWATT220AB, TO-220FPAB
Insulating voltage = 2000V DC
Capacitance = 12pF

DESCRIPTION

Dual center tap Schottky rectifier suited for SwitchMode Power Supply and high frequency DC to DC converters.

Packaged either in TO-220AB, ISOWATT220AB, TO-220FPAB, D²PAK or I²PAK, this device is especially intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



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ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit	
V _{RRM}	Repetitive peak reverse voltage			45	V	
I _{F(RMS)}	RMS forward current			20	A	
I _{F(AV)}	Average forward current $\delta = 0.5$	TO-220AB / D ² PAK / I ² PAK	T _c = 157°C	Per diode	7.5	A
		ISOWATT220AB / TO-220FPAB	T _c = 130°C	Per device	15	
I _{FSM}	Surge non repetitive forward current		tp = 10 ms Sinusoidal	150	A	
I _{RRM}	Repetitive peak reverse current		tp = 2 μ s square F = 1kHz	1	A	
I _{RSM}	Non repetitive peak reverse current		tp = 100 μ s square	2	A	
T _{stg}	Storage temperature range			-65 to +175	°C	
T _j	Maximum operating junction temperature *			175	°C	
dV/dt	Critical rate of rise of reverse voltage			10000	V/ μ s	

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$ thermal runaway condition for a diode on its own heatsink

THERMAL RESISTANCES

Symbol	Parameter			Value	Unit
R _{th(j-c)}	Junction to case	TO-220AB / D ² PAK / I ² PAK	Per diode	3.0	°C/W
			Total	1.7	
	ISOWATT220AB / TO-220FPAB	Per diode	5.5		
		Total	4.2		
R _{th(c)}		TO-220AB / D ² PAK / I ² PAK	Coupling	0.35	
		ISOWATT220AB / TO-220FPAB		2.9	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j (\text{diode 1}) = P (\text{diode 1}) \times R_{th(j-c)} (\text{per diode}) + P (\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (Per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	T _j = 25°C	V _R = V _{RRM}			100	μ A
		T _j = 125°C			5	15	mA
V _F *	Forward voltage drop	T _j = 125°C	I _F = 7.5 A		0.5	0.57	V
		T _j = 25°C	I _F = 15 A			0.84	
		T _j = 125°C	I _F = 15 A		0.65	0.72	

Pulse test : * tp = 380 μ s, $\delta < 2\%$

To evaluate the conduction losses use the following equation :

$$P = 0.42 \times I_{F(AV)} + 0.020 I_{F(RMS)}^2$$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

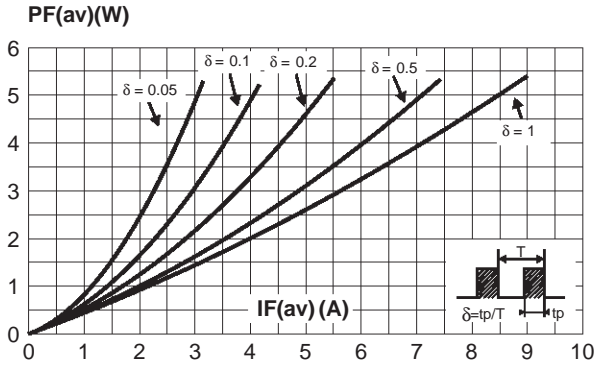


Fig. 2: Average current versus ambient temperature ($\delta = 0.5$, per diode).

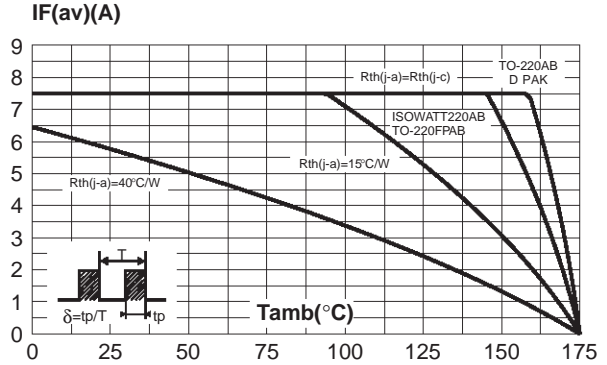


Fig. 3-1: Non repetitive surge peak forward current versus overload duration (maximum values, per diode) (TO-220AB and D²PAK).

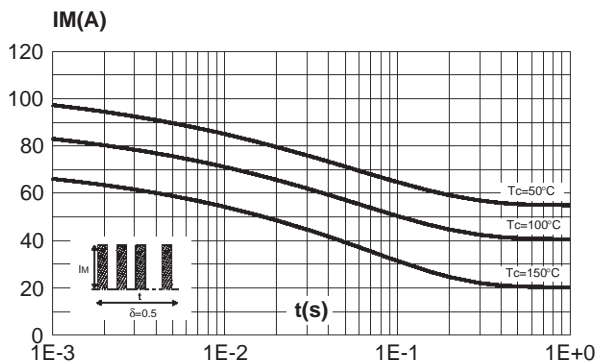


Fig. 3-2: Non repetitive surge peak forward current versus overload duration (maximum values, per diode) (ISOWATT220AB, TO-220FPAB).

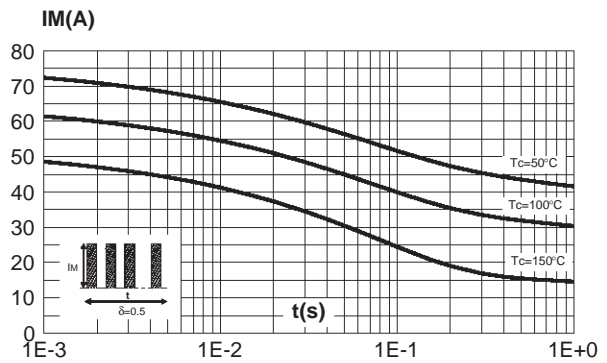


Fig. 4-1: Relative variation of thermal transient impedance junction to case versus pulse duration (per diode) (TO-220AB and D²PAK).

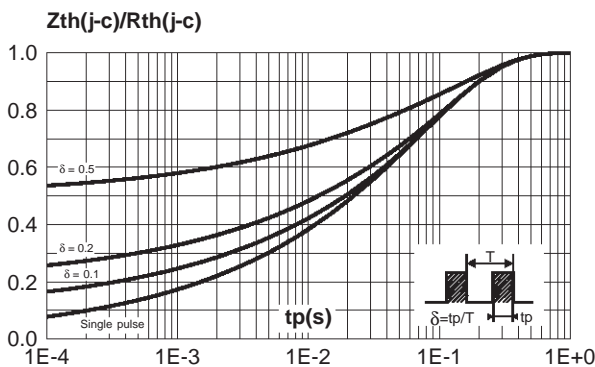


Fig. 4-2: Relative variation of thermal transient impedance junction to case versus pulse duration (per diode) (ISOWATT220AB, TO-220FPAB).

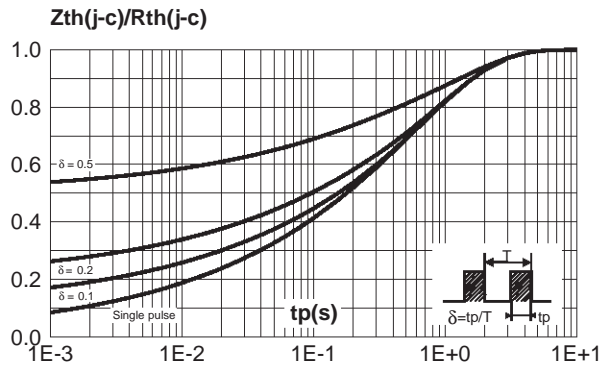


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values, per diode).

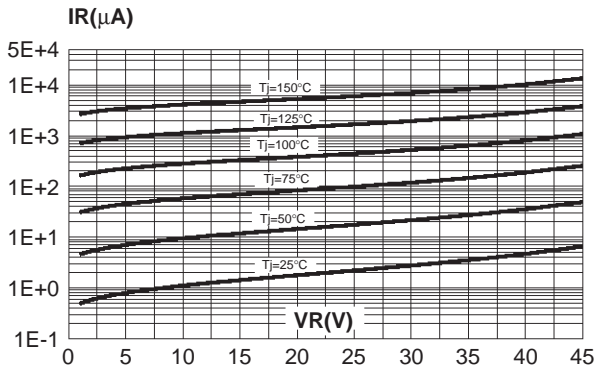


Fig. 6: Junction capacitance versus reverse voltage applied (typical values, per diode).

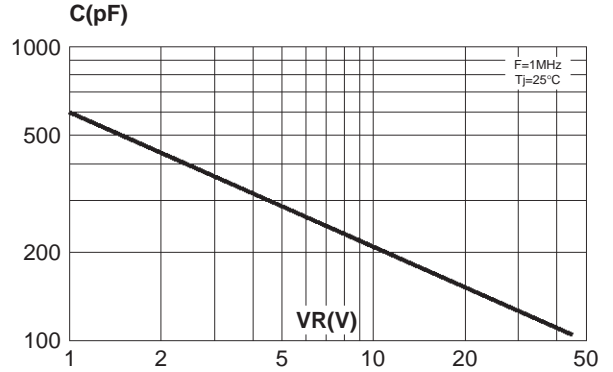


Fig. 7: Forward voltage drop versus forward current (maximum values, per diode).

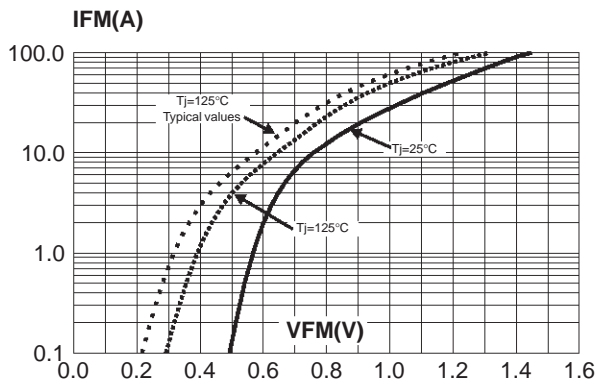
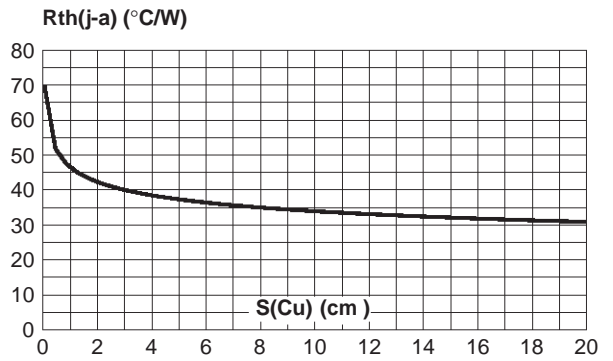
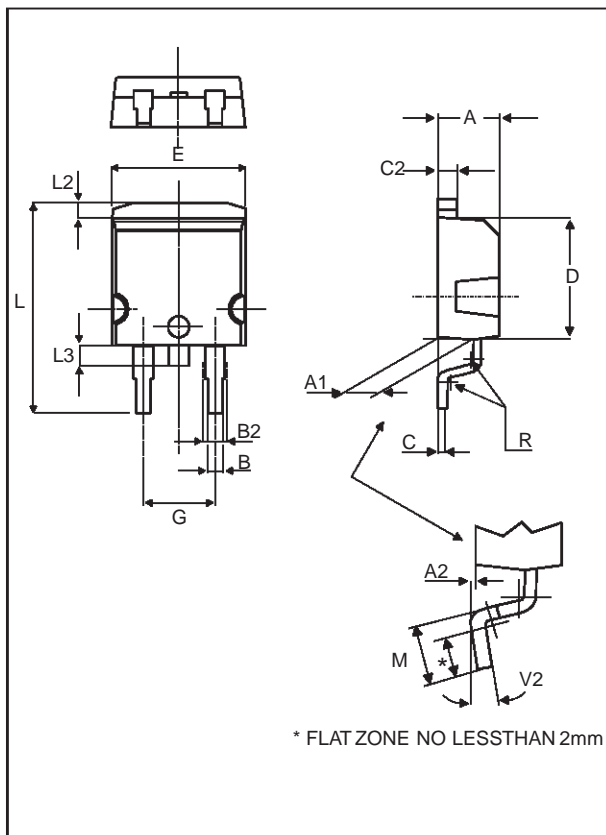


Fig. 8: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board, copper thickness: $35\mu m$).

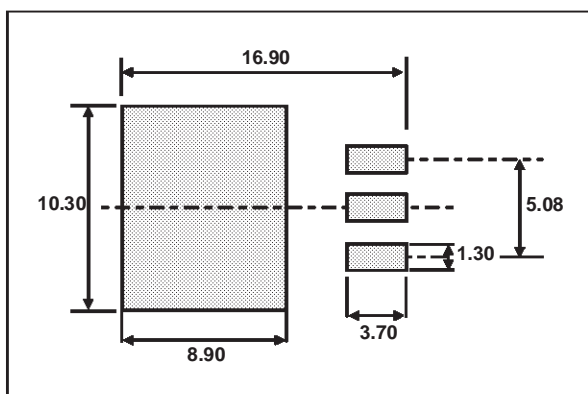


PACKAGE MECHANICAL DATA
D²PAK



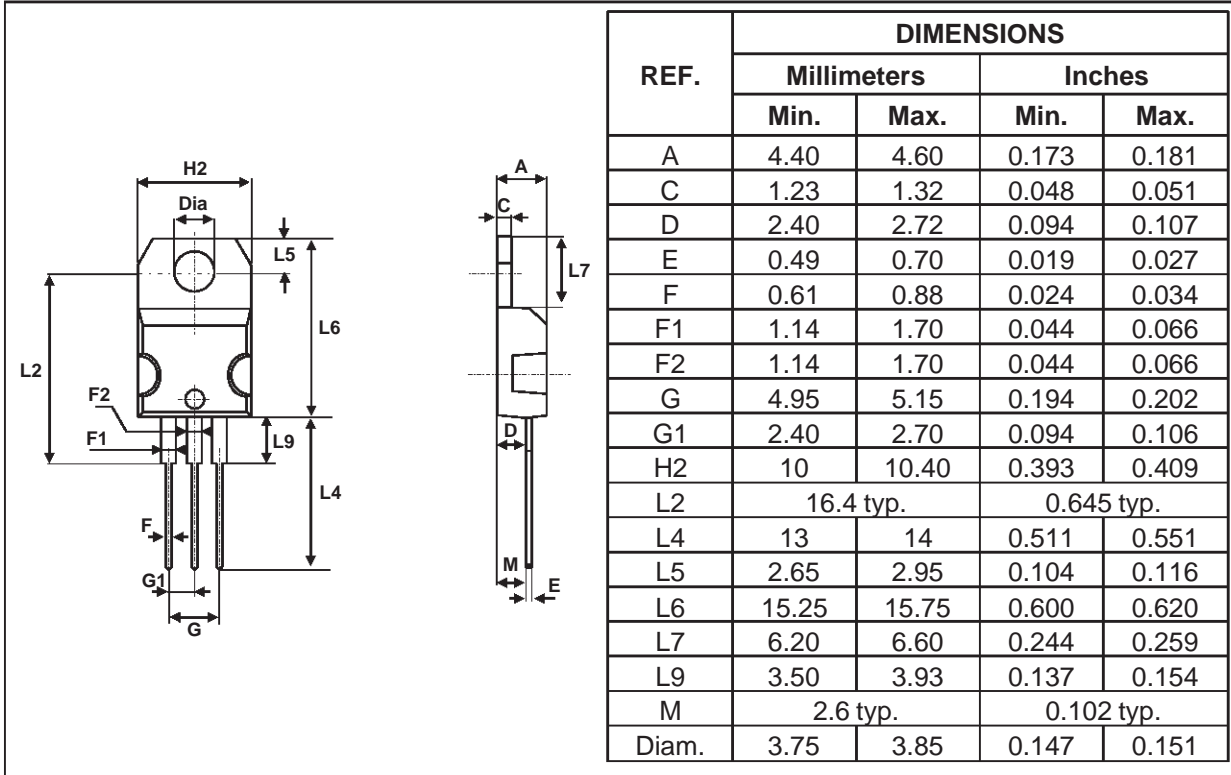
REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
B	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
C	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
E	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
M	2.40	3.20	0.094	0.126
R	0.40 typ.		0.016 typ.	
V2	0°	8°	0°	8°

FOOTPRINT DIMENSIONS (in millimeters)

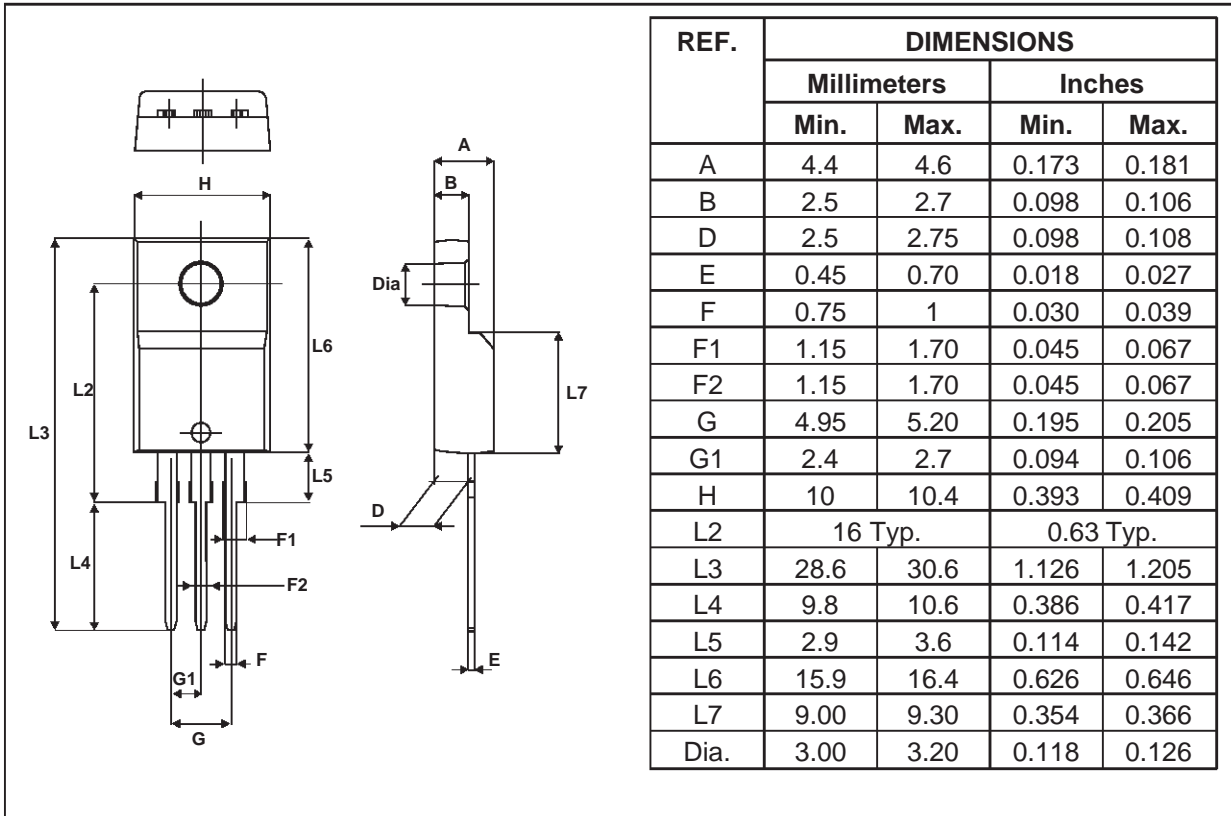


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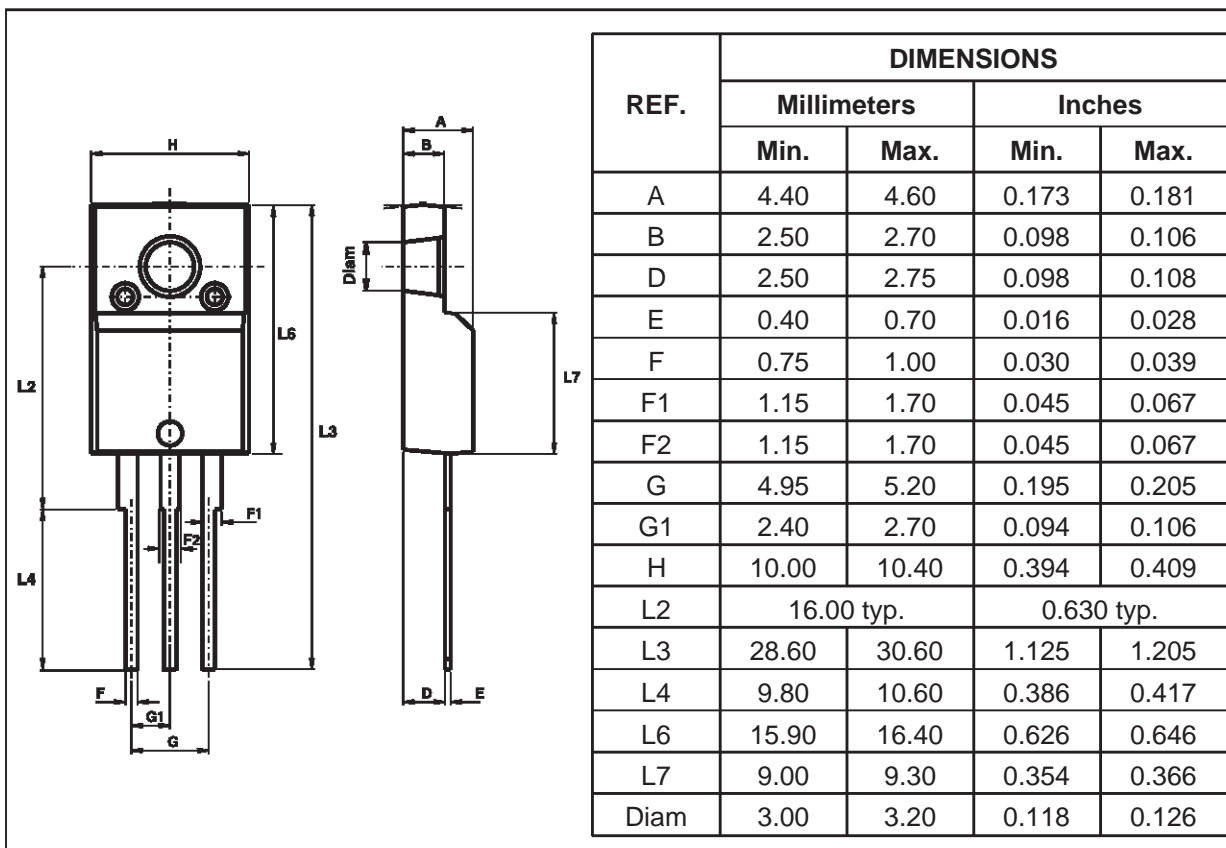
PACKAGE MECHANICAL DATA
TO-220AB



PACKAGE MECHANICAL DATA
TO-220FPAB

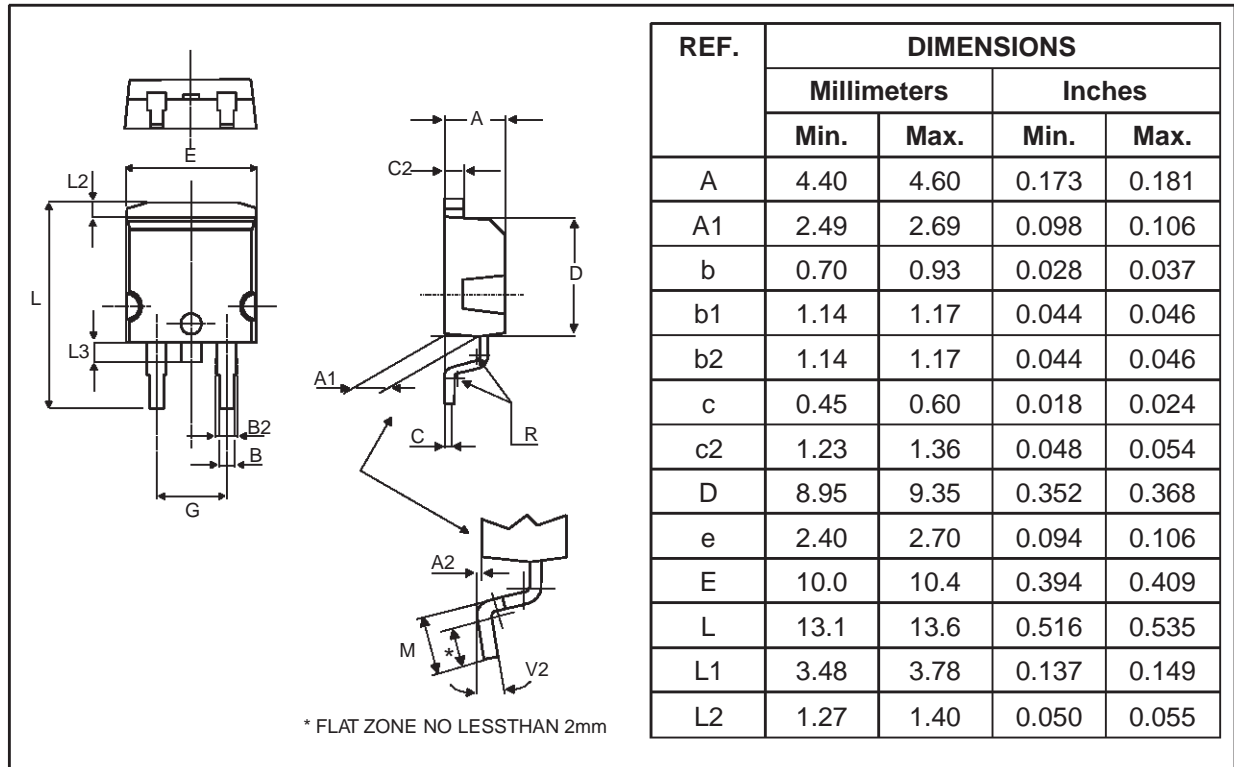


PACKAGE MECHANICAL DATA
ISOWATT220AB



STPS1545CT/CF/CG/CFP/CR

PACKAGE MECHANICAL DATA
I²PAK



Type	Marking	Package	Weight	Base qty	Delivery mode
STPS1545CT	STPS1545CT	TO-220AB	2.23 g.	50	Tube
STPS1545CF	STPS1545CF	ISOWATT220AB	2.08 g.	50	Tube
STPS1545CFP	STPS1545CFP	TO-220FPAB	2.0 g	50	Tube
STPS1545CG	STPS1545CG	D ² PAK	1.48 g.	50	Tube
STPS1545CG-TR	STPS1545CG	D ² PAK	1.48 g.	1000	Tape & reel
STPS1545CR	STPS1545CR	I ² PAK	1.49 g	50	Tube

- Cooling method: by conduction (C)
- Epoxy meets UL94,V0

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